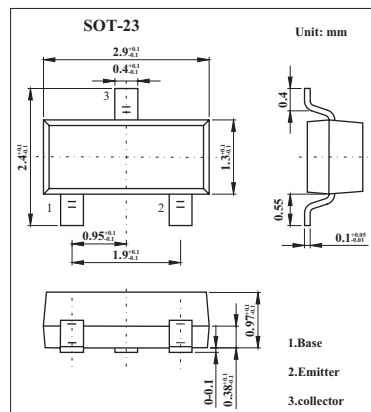


FMMT4400

■ Features

- General purpose transistors.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	40	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	600	mA
Power dissipation	P _{tot}	330	mW
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =0.1mA	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.1mA	6			V
Collector-emitter cut-off current	I _{CEX}	V _{CE} =35V V _{EB(off)} =0.4V			0.1	μA
Base cut-off current	I _{BEX}	V _{CE} =35V V _{EB(off)} =3V			0.1	μA
DC current gain *	h _{FE}	I _C =150mA, V _{CE} =1V	50		150	
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C =150mA, I _B =15mA I _C =500mA, I _B =50mA			0.4 0.75	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C =150mA, I _B =15mA I _C =500mA, I _B =50mA	0.75		0.95 1.2	V
Current-gain-bandwidth product	f _T	I _C =20mA, V _{CE} =10V f=100KHz	200			MHz
Output capacitance	C _{obo}	V _{CB} =5V, I _E =0, f=100KHz			6.5	pF
Input capacitance	C _{ibo}	V _{BE} =0.5V, I _C =0, f=100KHz			30	pF
Delay time	t _{on}	V _{CC} =30V, I _C =150mA, I _{B1} =15mA V _{BE(off)} =2V			35	ns
Storage time	t _{off}	V _{CC} =30V, I _C =150mA I _{B1} = I _{B2} =15mA			255	ns

* Pulse test: t_p ≤ 300 μs; d ≤ 0.02.

■ Marking

Marking	1KZ
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